




	<p>SI7784DP-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI7784DP-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 35A PPAK SO-8</p> <p>Datenblätter:  SI7784DP-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 3000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7784DP-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 30V 35A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	3000 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	5W (Ta), 27.7W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	35A (Tc)
Rds On (Max) @ Id, Vgs	6 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	45nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1600pF @ 15V
Verpackung	Tape & Reel (TR)


























SI7784DP-T1-GE3 ist neu im Original, Suche SI7784DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7784DP-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7784DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7774DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A PPAK SO-8</p>	 <p>SI7772DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 35.6A PPAK SO-8</p>	 <p>SI7788DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 50A PPAK SO-8</p>	 <p>SI7790DP-T1-E3 VISHAY Si7790DP-T1-E3 VISHAY</p>
 <p>SI7772DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 35.6A PPAK SO-8</p>	 <p>SI7774DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 60A PPAK SO-8</p>	 <p>SI7788DP-T1-E3 VISHAY VISHAY PAKSO-8</p>	 <p>SI7772DP-T1-E3 VISHAY VISHAY PAKSO-8</p>

heiße Teile

Mehr

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|---|---|--|---|--|
|  SI7720DN-T1-GE3 |  SI7726DN |  SI7726DN-T1-E3 |  SI7726DN-T1-GE3 |  SI7726DN-T1-GE3 |
|  SI7732DP-T1-GE3 |  SI7738DP |  SI7738DP-T1-3 |  SI7738DP-T1-E3 |  SI7738DP-T1-E3 |
|  SI7738DP-T1-GE3 |  SI7738DP-T1-GE3 |  SI7742DP-T1-E3 |  SI7742DP-T1-GE3 |  SI7742DP-T1-GE3 |
|  SI7748DP-T1-GE3 |  SI7748DP-T1-GE3 |  SI7758DP |  SI7758DP-T1-GE3 |  SI7758DP-T1-GE3 |
|  SI7772DP-T1-GE3 |  SI7772DP-T1-GE3 |  SI7774DP-T1-GE3 |  SI7774DP-T1-GE3 |  SI7774DP-T1-GE3 |
|  SI7788DP-T1-GE3 |  SI7788DP-T1-GE3 |  SI7790DP-T1-E3 |  SI7790DP-T1-GE3 |  SI7790DP-T1-GE3 |
|  SI7792DP-T1-GE3 |  SI7792DP-T1-GE3 |  SI7794DP-T1-GE3 |  SI7794DP-T1-GE3 |  SI7794DP-T1-GE3 |
|  SI7804DN |  SI7804DN-T1-E3 |  SI7804DN-T1-E3 |  SI7806ADN |  SI7806ADN-T1-E3 |
|  SI7806ADN-T1-E3 |  SI7806ADN-T1-E3-PBF |  SI7806ADN-T1-GE3 |  SI7806ADN-T1-GE3 |  SI7806AEDN-T1-E3 |
|  SI7806BDN |  SI7806BDN-T1-GE3 |  SI7806DN-T1-E3 |  SI7806DN-T1-GE3 |  SI7810DN |

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